



Phase out

## Standard Rectifier Module

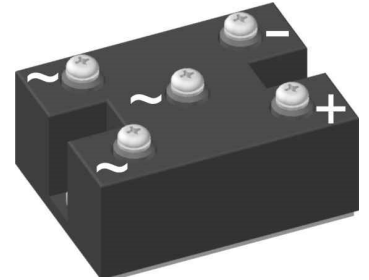
# PHASE OUT

3~ Rectifier Bridge

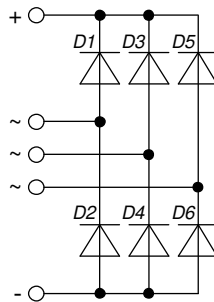
<b>3~ Rectifier</b>
$V_{RRM} = 1200\text{ V}$
$I_{DAV} = 120\text{ A}$
$I_{FSM} = 1500\text{ A}$

Part number

**VUO105-12NO7**



E72873



### Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

### Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

### Package: PWS-C

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Copper internally DCB isolated
- Advanced power cycling

**Recommended replacement: VUO160-12NO7**

### Disclaimer Notice

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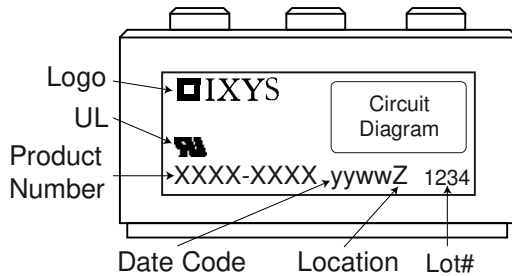
Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage					1300	V
$V_{RRM}$	max. repetitive reverse blocking voltage					1200	V
$I_R$	reverse current	$V_R = 1200$ V	$T_{VJ} = 25^\circ\text{C}$			100	$\mu\text{A}$
		$V_R = 1200$ V	$T_{VJ} = 150^\circ\text{C}$			2	mA
$V_F$	forward voltage drop	$I_F = 40$ A	$T_{VJ} = 25^\circ\text{C}$			1.09	V
		$I_F = 120$ A				1.38	V
		$I_F = 40$ A	$T_{VJ} = 125^\circ\text{C}$			1.00	V
		$I_F = 120$ A				1.36	V
$I_{DAV}$	bridge output current	$T_C = 105^\circ\text{C}$ rectangular	$T_{VJ} = 150^\circ\text{C}$ $d = \frac{1}{3}$			120	A
$V_{FO}$	threshold voltage	} for power loss calculation only				0.78	V
$r_F$	slope resistance					4.8	m $\Omega$
$R_{thJC}$	thermal resistance junction to case					0.8	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.3		K/W
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		155	W
$I_{FSM}$	max. forward surge current	$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			1.50	kA
		$t = 8,3$ ms; (60 Hz), sine	$V_R = 0$ V			1.62	kA
		$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 150^\circ\text{C}$			1.28	kA
		$t = 8,3$ ms; (60 Hz), sine	$V_R = 0$ V			1.38	kA
$I^2t$	value for fusing	$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			11.3	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine	$V_R = 0$ V			10.9	kA <sup>2</sup> s
		$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 150^\circ\text{C}$			8.13	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine	$V_R = 0$ V			7.87	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400$ V; $f = 1$ MHz	$T_{VJ} = 25^\circ\text{C}$		58		pF

**PHASE OUT**



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Package PWS-C		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			150	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				250		g
$M_D$	mounting torque		4.25		5.75	Nm
$M_T$	terminal torque		4.25		5.75	Nm
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	26.0			mm
$d_{Spb/Apb}$		terminal to backside	14.0			mm
$V_{ISOL}$	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V

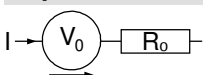


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO105-12NO7	VUO105-12NO7	Box	10	456713

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 150^{\circ}C$

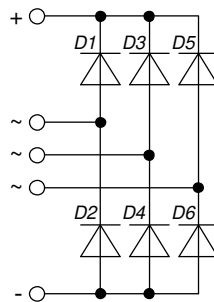
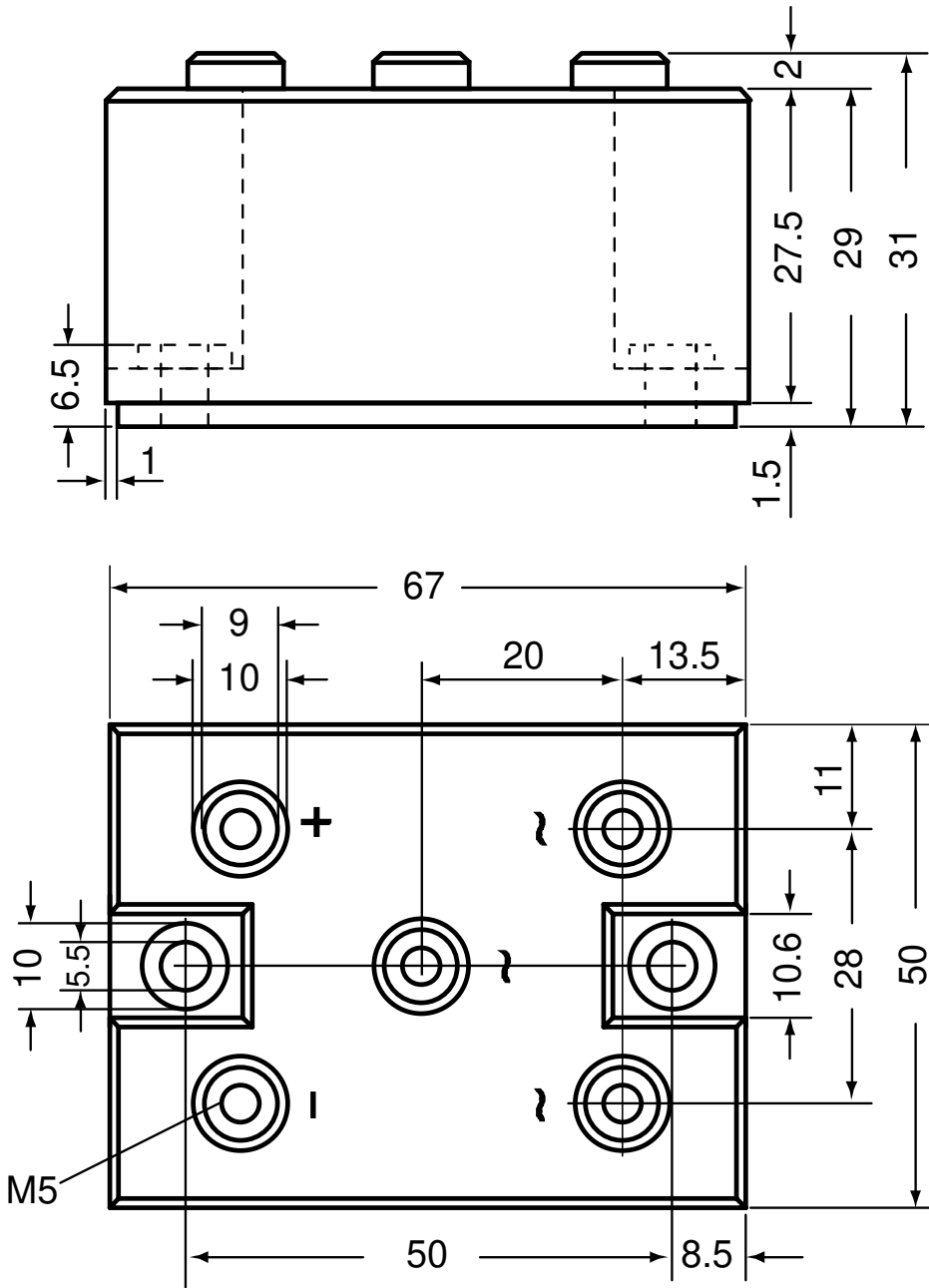


**Rectifier**

$V_{0\ max}$	threshold voltage	0.78	V
$R_{0\ max}$	slope resistance *	3.6	mΩ



Outlines PWS-C





**Rectifier**

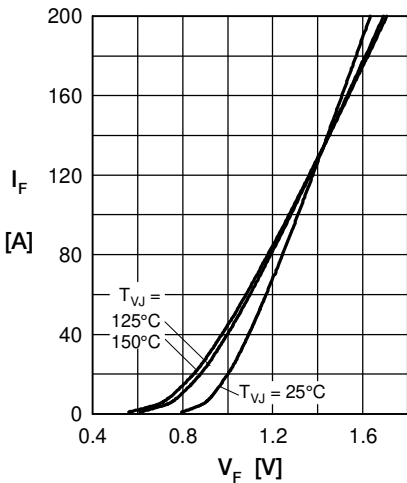


Fig. 1 Forward current versus voltage drop per diode

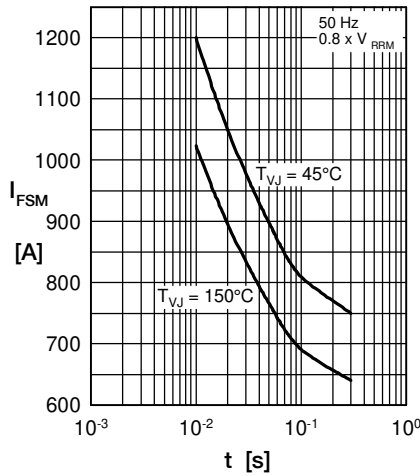


Fig. 2 Surge overload current vs. time per diode

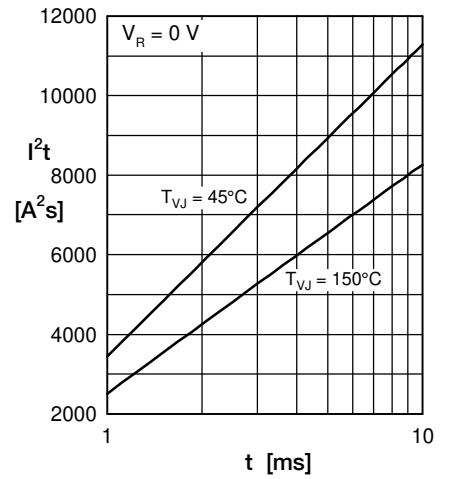


Fig. 3  $I^2t$  versus time per diode

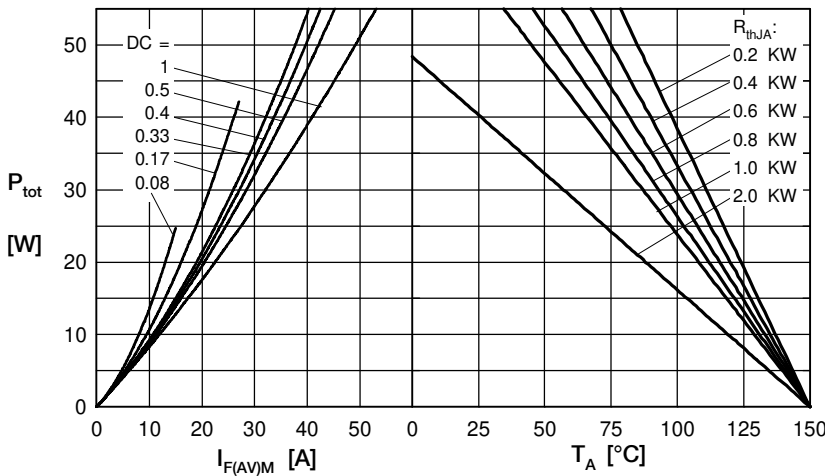


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

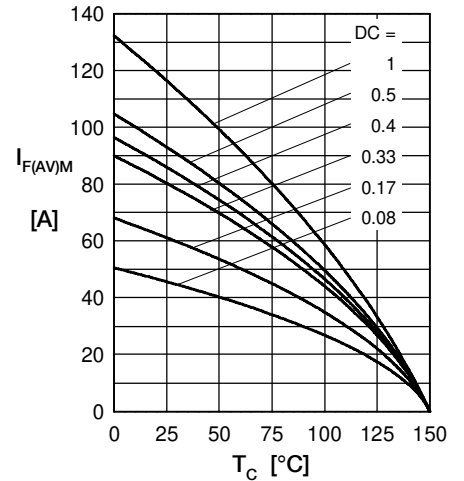


Fig. 5 Max. forward current vs. case temperature per diode

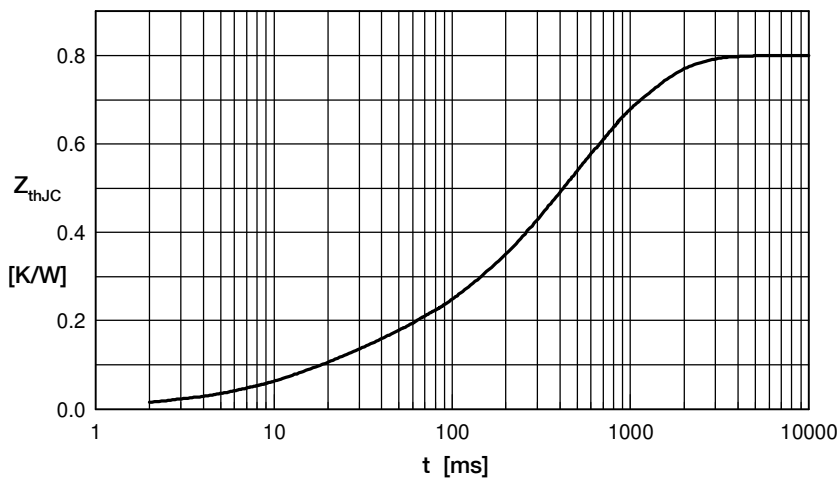


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for  $Z_{thJC}$  calculation:

i	$R_{th}$ (K/W)	$t_i$ (s)
1	0.100	0.020
2	0.014	0.010
3	0.192	0.225
4	0.281	0.800
5	0.213	0.580